CD4011A, CD4012A, CD4023A Typ s

COS/MOS NAND Gates

Quad 2 Input – CD4011A
Dual 4 Input – CD4012A
Triple 3 Input – CD4023A

The RCA-CD4011A, CD4012A, and CD-4023A NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of COS/MOS gates.

These types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

- Quiescent current specified to 15 V
- Maximum input leakage of 1 μA at 15 V (full package-temperature range)
- 1-V noise margin (full package-temperature range)

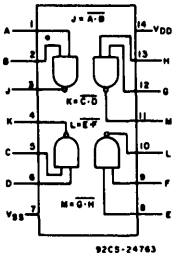
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

Characteristic	Min.	Max.	Units
Supply Voltage Range (over full package temperature range)	3	12	V

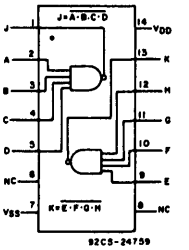
MAXIMUM RATINGS, *Absolute-Maximum Values:*

STORAGE-TEMPERATURE RANGE (T_{stg}) . . . . . –65 to +150°C
OPERATING-TEMPERATURE RANGE (T_A)
PACKAGE TYPES D, F, H . . . . . –55 to +125°C
PACKAGE TYPE E . . . . . –40 to +85°C
DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) . . . . . –0.5 to +15 V
POWER DISSIPATION PER PACKAGE (P_D):
FOR T_A = –40 to +60°C (PACKAGE TYPE E) . . . . . 500 mW
FOR T_A = +60 to +85°C (PACKAGE TYPE E) . . . . . Derate Linearly at 12 mW/°C to 200 mW
FOR T_A = –55 to +100°C (PACKAGE TYPES D, F) . . . . . 500 mW
FOR T_A = +100 to +125°C (PACKAGE TYPES D, F) . . Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (ALL PACKAGE TYPES) . . . . . 100 mW
INPUT VOLTAGE RANGE, ALL INPUTS . . . . . –0.5 to V_{DD} +0.5 V
LEAD TEMPERATURE (DURING SOLDERING).
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max . . . . . +265°C



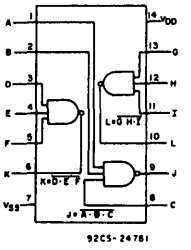
92CS-24763

CD4011A



92CS-24759

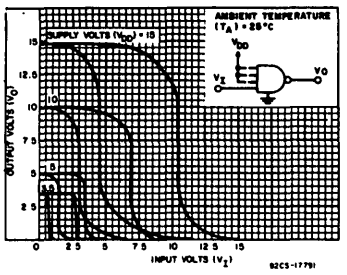
CD4012A



92CS-24781

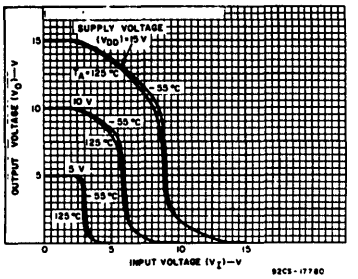
CD4023AH

Fig. 1 – Functional diagrams.



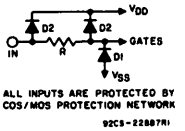
92CS-17791

Fig. 2 – Minimum & maximum voltage transfer characteristics.



92CS-17790

Fig. 3 – Typical voltage transfer characteristics as a function of temperature.



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK
92CS-22887R1

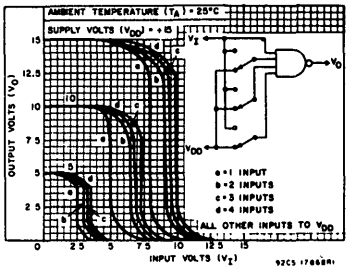


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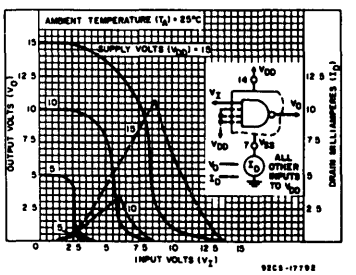
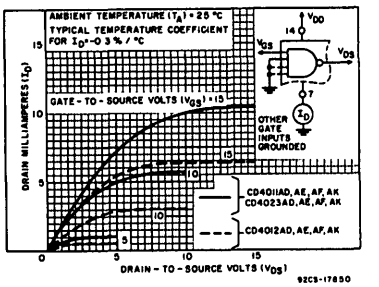
Fig. 4 – Typical multiple input switching transfer characteristics for CD4012A.



92CS-17792

Fig. 5 – Typical current & voltage transfer characteristics.



92CS-17850

Fig. 6 – Typical n-channel drain characteristics.

STATIC ELECTRICAL CHARACTERISTICS

Characteristic	Conditions			Limits at Indicated Temperatures (°C)								Units
				D,F,H Packages				E Package				
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	+25 Typ.	+25 Limit	+125	−40	+25 Typ.	+25 Limit	+85	
Quiescent Device Current, I_L Max.	–	–	5	0.05	0.001	0.05	3	0.5	0.005	0.5	15	μA
	–	–	10	0.1	0.001	0.1	6	5	0.005	5	30	
	–	–	15	2	0.02	2	40	50	0.5	50	500	
Output Voltage: L w-Level V_{OL}	–	0,5	5	0 Typ.; 0.05 Max.								V
	–	0,10	10	0 Typ.; 0.05 Max.								
High Level, V_{OH}	–	0,5	5	4.95 Min.; 5 Typ.								
	–	0,10	10	9.95 Min.; 10 Typ.								
Noise Immunity: Inputs Low, V_{NL}	3.6	–	5	1.5 Min.; 2.25 Typ.								V
	7.2	–	10	3 Min.; 4.5 Typ.								
Inputs High, V_{NH}	1.4	–	5	1.5 Min.; 2.25 Typ.;								
	2.8	–	10	3 Min.; 4.5 Typ.								
Noise Margin: Inputs Low, V_{NML}	4.5	–	5	1 Min.								V
	9	–	10	1 Min.								
Inputs High, V_{NMH}	0.5	–	5	1 Min.								
	1	–	10	1 Min.								
Output Drive Current: N-Channel (Sink) I_DN Min. CD4011A	0.5	–	5	0.31	0.5	0.25	0.175	0.145	0.5	0.12	0.095	mA
CD4023A	0.5	–	10	0.62	0.6	0.5	0.35	0.3	0.6	0.25	0.2	
CD4012A	0.5	–	5	0.15	0.25	0.12	0.085	0.072	0.25	0.06	0.05	
	0.5	–	10	0.31	0.6	0.25	0.175	0.155	0.6	0.13	0.105	
P-Channel (Source), I_DP Min. All Types	4.5	–	5	-0.31	-0.5	-0.25	-0.175	-0.145	-0.5	-0.12	-0.095	
	9.5	–	10	-0.75	-1.2	-0.6	-0.4	-0.35	-1.2	-0.3	-0.24	
Input Leakage Current, I_{IL}, I_{IH}	Any Input		15	$\pm 10^{-5}$ Typ.; ±1 Max.								μA

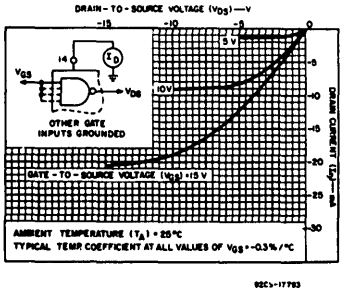


Fig. 7 — Typical p-channel drain characteristics.

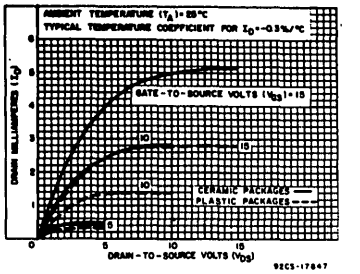


Fig. 8 — Minimum n-channel drain characteristics —CD4011A & CD4023A.

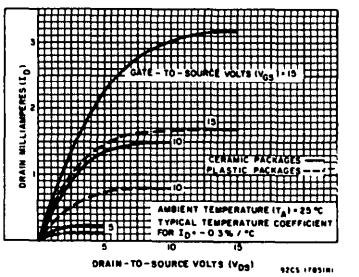


Fig. 9 — Typical n-channel drain characteristics.

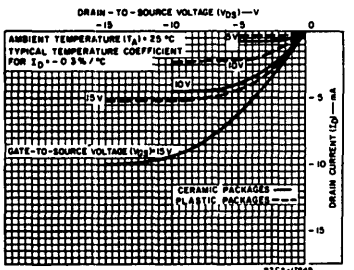


Fig. 10 — Minimum p-channel drain characteristics.

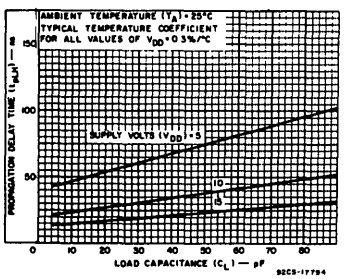


Fig. 11 — Typical low-to-high level propagation delay time vs. C_L.

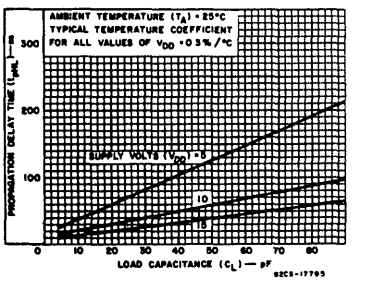


Fig. 12 — Typical high-to-low level propagation delay time vs. C_L — CD4011A, & CD4023A.

CD4011A, CD4012A, CD4023A Typ s

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, C_L = 15 pF, Input t_r, t_f = 20 ns, R_L = 200 KΩ

CHARACTERISTICS	TEST CONDITIONS		LIMITS				UNITS
			D,F,H Packages		*E Package*		
		V_{DD} (V)	Typ.	Max.	Typ.	Max.	
Propagation Delay Time: Low-to-High Level, t_{PLH}		5	50	75	50	100	ns
		10	25	40	25	50	
High-to-Low Level, t_{PHL} CD4011A and CD4023A		5	50	75	50	100	ns
		10	25	40	25	50	
CD4012A		5	100	150	100	200	ns
		10	50	75	50	100	
Transition Time: Low-to-High Level, t_{TLH}		5	75	100	75	125	ns
		10	40	60	40	75	
High-to-Low Level, t_{THL} CD4011A and CD4023A		5	75	125	75	150	ns
		10	50	75	50	100	
CD4012A		5	250	375	250	500	ns
		10	125	200	125	250	
Input Capacitance, C_I	Any Input		5	–	5	–	pF

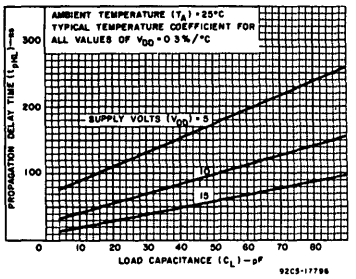


Fig. 13 – Typical high-to-low level propagation delay time vs. C_L – CD4012A.

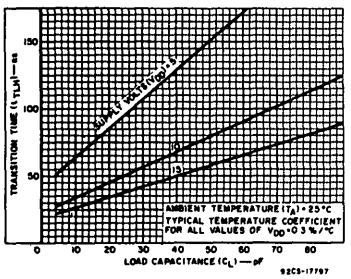


Fig. 14 – Typical low-to-high transition time vs. C_L.

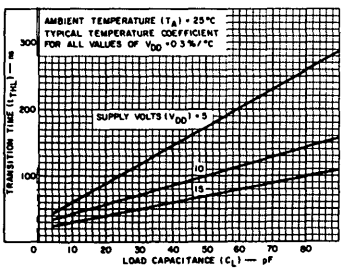


Fig. 15 – Typical high-to-low level transition time vs. C_L – CD4011A & CD4023A.

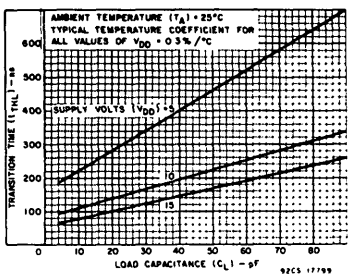


Fig. 16 – Typical high-to-low level transition time vs. C_L – CD4012A.

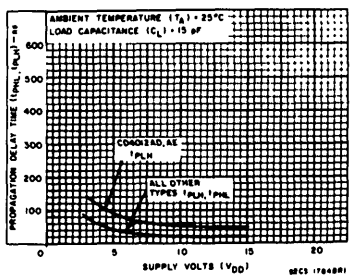


Fig. 17 – Minimum propagation delay time vs. V_{DD}.

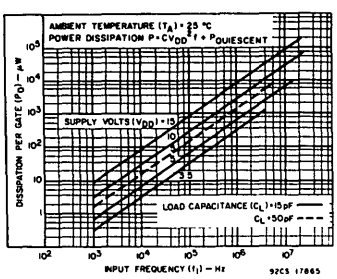


Fig. 18 – Typical dissipation characteristics.

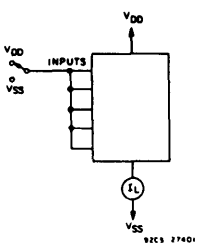


Fig. 19 – Quiescent device current test circuit.

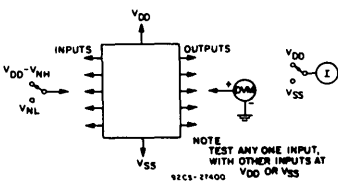


Fig. 20 – Noise immunity test circuit.

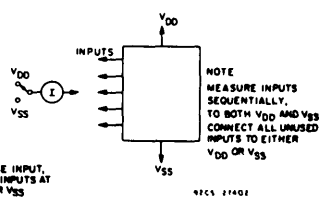


Fig. 21 – Input leakage current test circuit.